Low-Voltage CMOS Octal Buffer

With 5 V-Tolerant Inputs and Outputs (3-State, Inverting)

The MC74LCX240 is a high performance, inverting octal buffer operating from a 2.3 to 3.6 V supply. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A $V_{\rm I}$ specification of 5.5 V allows MC74LCX240 inputs to be safely driven from 5 V devices. The MC74LCX240 is suitable for memory address driving and all TTL level bus oriented transceiver applications.

Current drive capability is 24 mA at the outputs. The Output Enable (\overline{OE}) input, when HIGH, disables the outputs by placing them in a HIGH Z condition.

Features

- Designed for 2.3 to 3.6 V V_{CC} Operation
- 5 V Tolerant Interface Capability With 5 V TTL Logic
- Supports Live Insertion and Withdrawal
- I_{OFF} Specification Guarantees High Impedance When $V_{CC} = 0 V$
- LVTTL Compatible
- LVCMOS Compatible
- 24 mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current in All Three Logic States (10 μA)
 Substantially Reduces System Power Requirements
- Latchup Performance Exceeds 500 mA
- ESD Performance:
 - ♦ Human Body Model >2000 V
 - Machine Model >200 V
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant



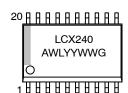
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MARKING DIAGRAMS

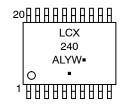


SOIC-20 WB DW SUFFIX CASE 751D





TSSOP-20 DT SUFFIX CASE 948E



A = Assembly Location

WL, L = Wafer Lot YY, Y = Year WW, W = Work Week G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

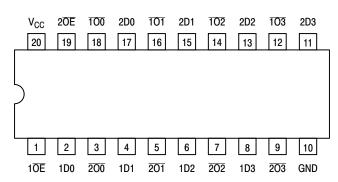
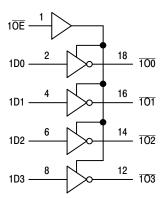


Figure 1. Pinout: 20-Lead (Top View)



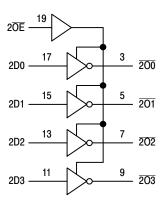


Figure 2. LOGIC DIAGRAM

PIN NAMES

Pins	Function
nŌĒ	Output Enable Inputs
1Dn, 2Dn	Data Inputs
10n, 20n	3-State Outputs

TRUTH TABLE

INP	JTS	OUTPUTS
10E 20E	1Dn 2Dn	10n, 20n
L	L	Н
L	Н	L
Н	Х	Z

H = High Voltage Level
L = Low Voltage Level
Z = High Impedance State
X = High or Low Voltage Le

X = High or Low Voltage Level and Transitions Are Acceptable; for I_{CC} reasons, DO NOT FLOAT Inputs

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74LCX240DTR2G	TSSOP-20 (Pb-Free)	2500 Tape & Reel
MC74LCX240DWR2G	SOIC-20 WB (Pb-Free)	1000 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MAXIMUM RATINGS

Symbol	Parameter	Value	Condition	Units
V _{CC}	DC Supply Voltage	-0.5 to +7.0		V
VI	DC Input Voltage	$-0.5 \le V_1 \le +7.0$		V
Vo	DC Output Voltage	$-0.5 \le V_O \le +7.0$	Output in 3-State	V
		$-0.5 \le V_O \le V_{CC} + 0.5$	Note 1	V
I _{IK}	DC Input Diode Current	-50	V _I < GND	mA
I _{OK}	DC Output Diode Current	-50	V _O < GND	mA
		+50	V _O > V _{CC}	mA
Io	DC Output Source/Sink Current	±50		mA
I _{CC}	DC Supply Current Per Supply Pin	±100		mA
I _{GND}	DC Ground Current Per Ground Pin	±100		mA
T _{STG}	Storage Temperature Range	-65 to +150		°C
MSL	Moisture Sensitivity		Level 1	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Output in HIGH or LOW State. I_O absolute maximum rating must be observed.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Тур	Max	Units
V _{CC}	Supply Voltage Operating Data Retention Only	2.0 1.5	3.3 3.3	3.6 3.6	V
VI	Input Voltage	0		5.5	V
Vo	Output Voltage HIGH or LOW State 3-State	0 0		V _{CC} 5.5	V
I _{OH}	HIGH Level Output Current, V _{CC} = 3.0 V – 3.6 V			-24	mA
l _{OL}	LOW Level Output Current, V _{CC} = 3.0 V - 3.6 V			24	mA
I _{OH}	HIGH Level Output Current, V _{CC} = 2.7 V - 3.0 V			-12	mA
l _{OL}	LOW Level Output Current, V _{CC} = 2.7 V - 3.0 V			12	mA
T _A	Operating Free-Air Temperature	-40		+125	°C
Δt/ΔV	Input Transition Rise or Fall Rate, V_{IN} from 0.8 V to 2.0 V, V_{CC} = 3.0 V	0		10	ns/V

DC ELECTRICAL CHARACTERISTICS

			T _A = -40°C to +85°C		$T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$ $T_A = -40^{\circ}\text{C to } +125^{\circ}\text{C}$		to +125°C		
Symbol	Characteristic	Condition	Min	Max	Min	Max	Units		
V _{IH}	HIGH Level Input Voltage (Note 2)	2.7 V ≤ V _{CC} ≤ 3.6 V	2.0		2.0		V		
V_{IL}	LOW Level Input Voltage (Note 2)	2.7 V ≤ V _{CC} ≤ 3.6 V		0.8		0.8	V		
V _{OH}	HIGH Level Output Voltage	$2.7 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{I}_{OH} = -100 \mu\text{A}$	V _{CC} - 0.2		V _{CC} - 0.2		V		
		$V_{CC} = 2.7 \text{ V}; I_{OH} = -12 \text{ mA}$	2.2		2.2				
		$V_{CC} = 3.0 \text{ V; } I_{OH} = -18 \text{ mA}$	2.4		2.4				
		V _{CC} = 3.0 V; I _{OH} = -24 mA	2.2		2.2				

^{2.} These values of V_I are used to test DC electrical characteristics only.

DC ELECTRICAL CHARACTERISTICS (Continued)

			$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$		T _A = -40°C	to +125°C	
Symbol	Characteristic	Condition	Min	Max	Min	Max	Units
V _{OL}	LOW Level Output Voltage	$2.7 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{ I}_{OL} = 100 \mu\text{A}$		0.2		0.2	٧
		V _{CC} = 2.7 V; I _{OL} = 12 mA		0.4		0.4	
		V _{CC} = 3.0 V; I _{OL} = 16 mA		0.4		0.4	
		V _{CC} = 3.0 V; I _{OL} = 24 mA		0.55		0.6	
I _{OZ}	3-State Output Current	$V_{CC} = 3.6 \text{ V}, V_{IN} = V_{IH} \text{ or } V_{IL}, V_{OUT} = 0 \text{ to } 5.5 \text{ V}$		±5		±5	μΑ
I _{OFF}	Power Off Leakage Current	$V_{CC} = 0$, $V_{IN} = 5.5 \text{ V or } V_{OUT} = 5.5 \text{ V}$		10		10	μΑ
I _{IN}	Input Leakage Current	V _{CC} = 3.6 V, V _{IN} = 5.5 V or GND		±5		±5	μΑ
I _{CC}	Quiescent Supply Current	V _{CC} = 3.6 V, V _{IN} = 5.5 V or GND		10		10	μΑ
ΔI_{CC}	Increase in I _{CC} per Input	$2.3 \le V_{CC} \le 3.6 \text{ V}; V_{IH} = V_{CC} - 0.6 \text{ V}$		500		500	μΑ

AC CHARACTERISTICS (t_R = t_F = 2.5 ns; C_L = 50 pF; R_L = 500 $\Omega)$

				Limits T _A = -40°C to +125°C			
			TA				
			V _{CC} = 3.0	V to 3.6 V	V _{CC} = 2.7 V		
Symbol	Parameter	Waveform	Min	Max	Max	Units	
t _{PLH} t _{PHL}	Propagation Delay Input to Output	1	1.5 1.5	6.5 6.5	7.5 7.5	ns	
t _{PZH} t _{PZL}	Output Enable Time to High and Low Level	2	1.5 1.5	8.0 8.0	9.0 9.0	ns	
t _{PHZ} t _{PLZ}	Output Disable Time From High and Low Level	2	1.5 1.5	7.0 7.0	8.0 8.0	ns	
toshl toslh	Output-to-Output Skew (Note 3)			1.0 1.0		ns	

Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device.
 The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

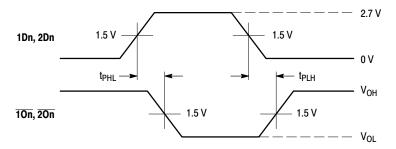
DYNAMIC SWITCHING CHARACTERISTICS

			T _A = +25°C			
Symbol	Characteristic	Condition	Min	Тур	Max	Units
V _{OLP}	Dynamic LOW Peak Voltage (Note 4)	V_{CC} = 3.3 V, C_L = 50 pF, V_{IH} = 3.3 V, V_{IL} = 0 V		0.8		V
V _{OLV}	Dynamic LOW Valley Voltage (Note 4)	$V_{CC} = 3.3 \text{ V}, C_L = 50 \text{ pF}, V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$		0.8		V

^{4.} Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

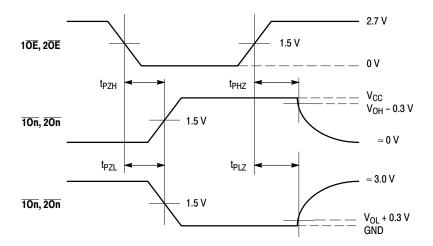
CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Parameter Condition		Units
C _{IN}	Input Capacitance	V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC}	7	pF
C _{OUT}	Output Capacitance	V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC}	8	pF
C _{PD}	Power Dissipation Capacitance	10 MHz, V _{CC} = 3.3 V, V _I = 0 V or V _{CC}	25	pF



WAVEFORM 1 - PROPAGATION DELAYS

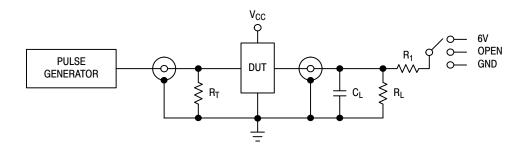
 t_R = t_F = 2.5 ns, 10% to 90%; f = 1 MHz; t_W = 500 ns



WAVEFORM 2 - OUTPUT ENABLE AND DISABLE TIMES

 $t_R = t_F = 2.5 \text{ ns}, 10\% \text{ to } 90\%; f = 1 \text{ MHz}; t_W = 500 \text{ ns}$

Figure 3. Waveforms



TEST	SWITCH
t _{PLH} , t _{PHL}	Open
t _{PZL} , t _{PLZ}	6V
Open Collector/Drain t _{PLH} and t _{PHL}	6V
t _{PZH} , t _{PHZ}	GND

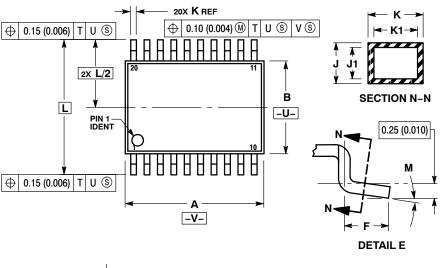
 C_L = 50 pF or equivalent (Includes jig and probe capacitance) R_L = R_1 = 500 Ω or equivalent

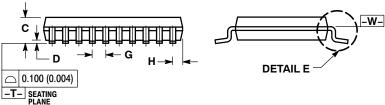
 $R_T = Z_{OUT}$ of pulse generator (typically 50 Ω)

Figure 4. Test Circuit

PACKAGE DIMENSIONS

TSSOP-20 CASE 948E ISSUE D



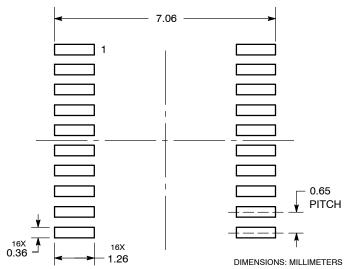


- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION:

 - 2. CONTROLLING DIMENSION:
 MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE
 MOLD FLASH, PROTRUSIONS OR GATE
 BURRS. MOLD FLASH OR GATE BURRS
 SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 4. DIMENSION B DOES NOT INCLUDE
 INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION.
 SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 5. DIMENSION K DOES NOT INCLUDE
 DAMBAR PROTRUSION. ALLOWABLE
 DAMBAR PROTRUSION. SHALL BE 0.08
 (0.003) TOTAL IN EXCESS OF THE K
 DIMENSION AT MAXIMUM MATERIAL (U.U.S.) TO TALL IN EXCESS OF THE K
 DIMENSION AT MAXIMUM MATERIAL
 CONDITION.
 6. TERMINAL NUMBERS ARE SHOWN FOR
 REFERENCE ONLY.
 7. DIMENSION A AND B ARE TO BE
 DETERMINED AT DATUM PLANE -W-.

DETERMINED AT DATOM FLAME -W							
	MILLIN	IETERS	INC	HES			
DIM	MIN	MAX	MIN	MAX			
Α	6.40	6.60	0.252	0.260			
В	4.30	4.50	0.169	0.177			
С		1.20		0.047			
D	0.05	0.15	0.002	0.006			
F	0.50	0.75	0.020	0.030			
G	0.65	BSC	0.026 BSC				
Н	0.27	0.37	0.011	0.015			
J	0.09	0.20	0.004	0.008			
J1	0.09	0.16	0.004	0.006			
K	0.19	0.30	0.007	0.012			
K1	0.19	0.25	0.007	0.010			
L	6.40		0.252 BSC				
М	0°	8°	0°	8°			

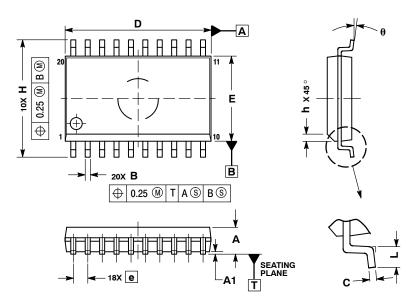
SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SO-20 WB CASE 751D-05 **ISSUE H**

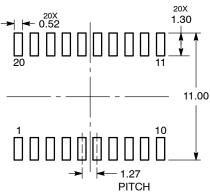


NOTES:

- DIMENSIONS ARE IN MILLIMETERS.
 INTERPRET DIMENSIONS. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
- DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS	
DIM	MIN	MAX
Α	2.35	2.65
A1	0.10	0.25
В	0.35	0.49
С	0.23	0.32
D	12.65	12.95
E	7.40	7.60
е	1.27 BSC	
Н	10.05	10.55
h	0.25	0.75
L	0.50	0.90
θ	0 °	7 °

RECOMMENDED SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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